

# ZXTP19100CG 100V PNP medium transistor in SOT223

### **Summary**

 $BV_{CEO} > -100V$ 

 $BV_{ECO} > -7V$ 

 $I_{C(cont)} = 2A$ 

 $V_{CE(sat)} < -130 \text{mV} @ -1 \text{A}$ 

 $R_{CE(sat)} = 100 m\Omega$ 

 $P_{D} = 3.0W$ 

Complementary part number ZXTN19100CG

### **Description**

Packaged in the SOT223 outline this new low saturation PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

### **Features**

- · High Gain
- · Low saturation voltage
- · High peak current

### **Applications**

- · High side driver
- · Motor drive
- · Load disconnect switch

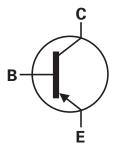
### **Ordering information**

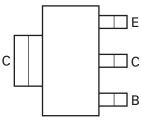
Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19100CGTA	7	12	1000

## **Device marking**

ZXTP19100C







Pinout - top view

## **Absolute maximum ratings**

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V <sub>CBO</sub>	-110	V
Collector-Emitter voltage (forward blocking)	V <sub>CEX</sub>	-110	V
Collector-Emitter voltage	V <sub>CEO</sub>	-100	V
Emitter-Collector voltage (reverse blocking)	V <sub>ECO</sub>	-7	V
Emitter-Base voltage	V <sub>EBO</sub>	-7	V
Continuous Collector current(c)	I <sub>C</sub>	-2	Α
Base current	I <sub>B</sub>	-1	Α
Peak pulse current	I <sub>CM</sub>	-3	Α
Power dissipation at T <sub>A</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	1.2	W
Linear derating factor		9.6	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(b)</sup>	P <sub>D</sub>	1.6	W
Linear derating factor		12.8	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(c)</sup>	P <sub>D</sub>	3.0	W
Linear derating factor		24	mW/°C
Power dissipation at T <sub>A</sub> =25°C <sup>(d)</sup>	P <sub>D</sub>	5.3	W
Linear derating factor		42	mW/°C
Power dissipation at T <sub>C</sub> =25°C <sup>(e)</sup>	P <sub>D</sub>	10.2	W
Linear derating factor		81	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

### Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	104	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\Theta JA}$	78	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\Theta JA}$	42	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\Theta JA}$	23.5	°C/W
Junction to case <sup>(e)</sup>	$R_{\Theta JC}$	12.3	°C/W

### NOTES:

<sup>(</sup>a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions

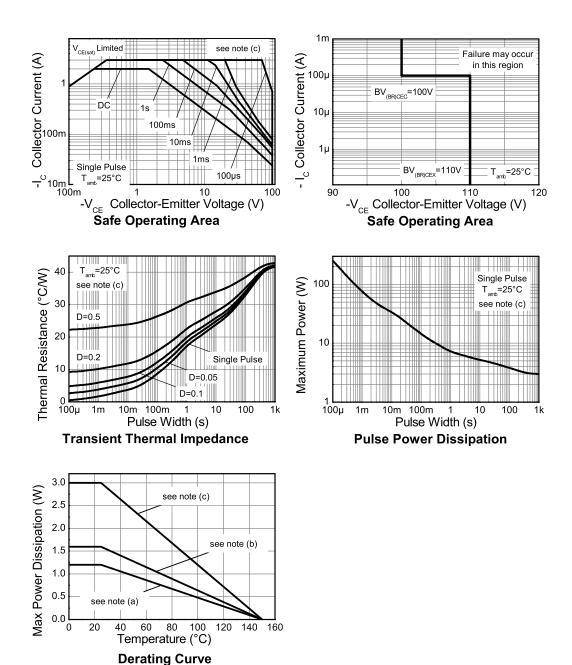
<sup>(</sup>b) Mounted on 25mm x 25mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

<sup>(</sup>c) Mounted on 50mm x 50mm x 0.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

<sup>(</sup>d) As (c) above measured at t<5 seconds.

<sup>(</sup>e) Junction to case (collector tab). Typical

### Thermal characteristics



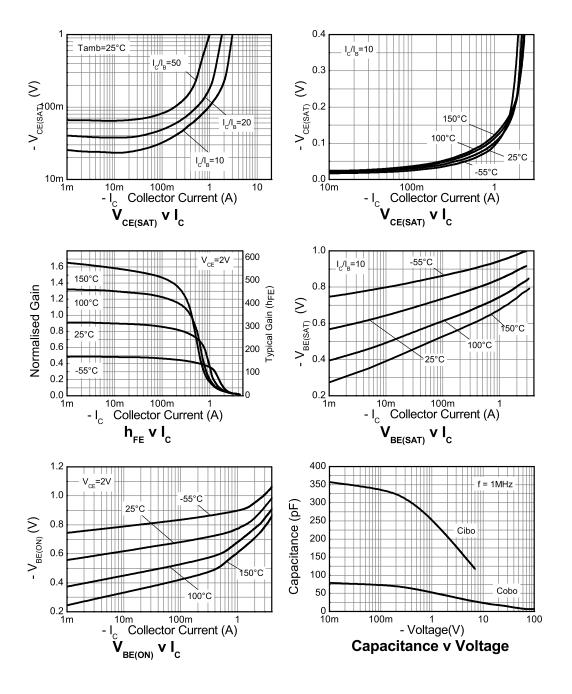
# Electrical characteristics (at T<sub>amb</sub> = 25°C unless otherwise stated)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV <sub>CBO</sub>	-110	-135		V	I <sub>C</sub> = -100μA
Collector-Emitter breakdown voltage	BV <sub>CEO</sub>	-100	-135		V	I <sub>C</sub> = -10mA <sup>(*)</sup>
Collector-Base breakdown voltage (forward blocking)	BV <sub>CEX</sub>	-110	-130		V	I <sub>C</sub> = -100μA
Emitter-Collector breakdown voltage (reverse blocking)	BV <sub>ECX</sub>	-7	-8.3		V	$I_E = -100\mu A$ , $R_{BC} < 1k\Omega$ or 0.25V > $V_{BC} > -0.25V$
Emitter-Collector breakdown voltage (reverse blocking)	BV <sub>ECO</sub>	-7	-8.7		V	I <sub>E</sub> = -100μA
Emitter-Base breakdown voltage	BV <sub>EBO</sub>	-7	-8.3		V	$I_E = -100\mu A$
Collector-Base cut-off	I <sub>CBO</sub>		<1	-50	nA	V <sub>CB</sub> = -110V
current				-0.5	μΑ	$V_{CB} = -110V, T_{amb} = 100^{\circ}C$
Emitter cut-off current	I <sub>EBO</sub>		<1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-Emitter	V <sub>CE(sat)</sub>		-100	-130	mV	$I_C = -0.5A$ , $I_B = -20mA^{(*)}$
saturation voltage			-100	-125	mV	$I_C = -1A$ , $I_B = -100 \text{mA}^{(*)}$
			-180	-230	mV	$I_C = -1A$ , $I_B = -50mA^{(*)}$
			-220	-295	mV	$I_C = -2A$ , $I_B = -200 \text{mA}^{(*)}$
Base-Emitter saturation voltage	V <sub>BE(sat)</sub>		-890	-1000	mV	$I_C = -2A$ , $I_B = -200 \text{mA}^{(*)}$
Base-Emitter turn-on voltage	V <sub>BE(on)</sub>		-840	-950	mV	$I_C = -2A$ , $V_{CE} = -2V^{(*)}$
Static forward current	h <sub>FE</sub>	200	300	500		$I_C = -100 \text{mA}, V_{CE} = -2V^{(*)}$
transfer ratio		70	130			$I_C = -1A$ , $V_{CE} = -2V^{(*)}$
		20	28			$I_C = -2A$ , $V_{CE} = -2V^{(*)}$
Transition frequency	f <sub>T</sub>		142		MHz	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -10V f = 50MHz
Input capacitance	C <sub>ibo</sub>		291	400	рF	V <sub>EB</sub> = -0.5V, f = 1MHz <sup>(*)</sup>
Output capacitance	C <sub>obo</sub>		23.5	40	pF	V <sub>CB</sub> = -10V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		24.7		ns	
Rise time	t <sub>r</sub>		22.4		ns	$I_C = -500 \text{mA}, V_{CC} = -10 \text{V},$
Storage time	t <sub>s</sub>		660		ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall time	t <sub>f</sub>		107		ns	$R_b = 100\Omega$ , $R_c = 20\Omega$

### NOTES:

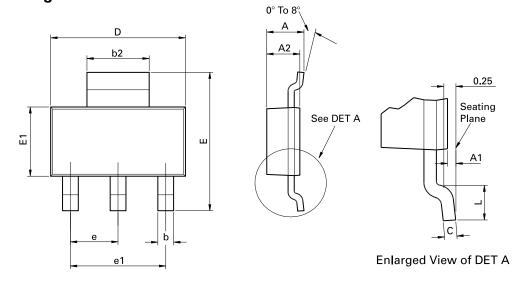
(\*) Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s; duty cycle  $\leq$  2%.

## **Typical characteristics**



# **ZXTP19100CG**

## Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
Dilli.	Min.	Max.	Min.	Max.	יייום.	Min.	Max.	Min.	Max.
Α	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	е	2.30	BSC	0.090	5 BSC
A2	1.55	1.65	0.0610	0.0649	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

# **ZXTP19100CG**

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